

R Zallen

List of Publications by Year in descending order

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186265

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46
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2184
citing authors

#	ARTICLE	IF	CITATIONS
1	Infrared reflectivity and lattice fundamentals in anatase TiO ₂ s. Physical Review B, 1997, 55, 7014-7017.	3.2	274
2	Lattice Vibrations and Interlayer Interactions in Crystalline As ₂ S ₃ and As ₂ Se ₃ . Physical Review B, 1971, 3, 4257-4273.	3.2	257
3	The optical absorption edge of brookite TiO ₂ . Solid State Communications, 2006, 137, 154-157.	1.9	180
4	Influence of pressure and temperature on phonons in molecular chalcogenides: Crystalline As ₄ S ₄ and S ₄ N ₄ . Physical Review B, 1978, 18, 5775-5798.	3.2	152
5	Electronic Structure of Crystalline and Amorphous As ₂ S ₃ and As ₂ Se ₃ . Physical Review Letters, 1971, 26, 1564-1567.	7.8	124
6	Raman studies of sol-gel alumina: Finite-size effects in nanocrystalline AlO(OH). Physical Review B, 1993, 48, 15626-15637.	3.2	91
7	Raman-scattering depth profile of the structure of ion-implanted GaAs. Physical Review B, 1988, 37, 4609-4617.	3.2	84
8	Pressure-optical studies of GeS ₂ glasses and crystals: Implications for network topology. Physical Review B, 1982, 25, 781-792.	3.2	81
9	Photoelastic trends for amorphous and crystalline solids of differing network dimensionality. Physical Review B, 1981, 24, 4652-4665.	3.2	75
10	Optical properties of ion-implanted GaAs: The observation of finite-size effects in GaAs microcrystals. Physical Review B, 1989, 40, 1064-1073.	3.2	74
11	Inter-polytype conversion and layer-layer coupling in PbI ₂ . Solid State Communications, 1975, 17, 1561-1566.	1.9	73
12	Interband spectra of As ₂ S ₃ and As ₂ Se ₃ crystals and glasses. Solid State Communications, 1972, 10, 293-296.	1.9	71
13	Effect of pressure on optical properties of crystalline As ₂ S ₃ . Physical Review B, 1980, 22, 3866-3876.	3.2	63
14	Lattice Vibrations in Trigonal HgS. Physical Review B, 1970, 1, 4058-4070.	3.2	60
15	The effect of temperature on libron frequencies in molecular crystals: Implications for TTF-TCNQ. Solid State Communications, 1979, 31, 557-561.	1.9	60
16	Electronic structure of S ₈ . Physical Review B, 1975, 12, 1493-1500.	3.2	59
17	Infrared activity in the Aurivillius layered ferroelectric SrBi ₂ Ta ₂ O ₉ . Physical Review B, 1998, 57, 5715-5723.	3.2	58
18	Raman scattering studies of silicon implanted gallium arsenide: The role of amorphicity. Journal of Applied Physics, 1986, 59, 1946-1951.	2.5	52

#	ARTICLE	IF	CITATIONS
19	Ferroelastic phase in SrBi ₂ Ta ₂ O ₉ and study of the ferroelectric phase-transition dynamics. Applied Physics Letters, 2002, 81, 1056-1058.	3.3	52
20	Plasma edge and band structure of cubic HgS. Solid State Communications, 1970, 8, 1291-1294.	1.9	50
21	The lattice polarizability of PbI ₂ . Solid State Communications, 1976, 18, 811-814.	1.9	48
22	The solid state transition in pyrene. Chemical Physics Letters, 1976, 39, 85-89.	2.6	42
23	Characterization of nanophase titania particles synthesized using <i>in situ</i> steric stabilization. Journal of Materials Research, 1997, 12, 1755-1765.	2.6	40
24	Raman spectra of As ₄ S ₄ polymorphs: Structural implications for amorphous As ₂ S ₃ films. Solid State Communications, 1979, 30, 357-360.	1.9	38
25	Infrared studies of hole-plasmon excitations in heavily-doped p-type MBE-grown GaAs:C. Physical Review B, 2000, 62, 4501-4510.	3.2	38
26	The effect of pressure on optical properties of As ₂ S ₃ glass. Journal of Non-Crystalline Solids, 1980, 35-36, 1255-1259.	3.1	37
27	Surface and bulk photoresponse of crystalline As ₂ S ₃ . Physical Review B, 1974, 9, 4306-4313.	3.2	35
28	Quenching of photoconductivity and luminescence in natural crystals of mercury sulphide. Journal of Physics C: Solid State Physics, 1971, 4, 1890-1897.	1.5	29
29	Bond Paths and van der Waals Interactions in Orpiment, As ₂ S ₃ . Journal of Physical Chemistry A, 2010, 114, 6550-6557.	2.5	29
30	Intervalenceband and plasmon optical absorption in heavily doped GaAs:C. Journal of Applied Physics, 2002, 91, 171.	2.5	24
31	Surface charging effects on valence band spectra in X-ray photoemission: Crystalline and Amorphous As ₂ S ₃ . Solid State Communications, 1976, 20, 793-797.	1.9	23
32	Polarization-dependent optical properties of orthorhombic sulfur in the ultraviolet. Physical Review B, 1976, 14, 808-813.	3.2	20
33	Raman-scattering and optical studies of argon-etched GaAs surfaces. Physical Review B, 1991, 43, 9678-9686.	3.2	17
34	Resonant Raman-active acoustic phonons in ion-implanted GaAs. Physical Review B, 1988, 38, 6097-6106.	3.2	14
35	Raman-scattering studies of implantation-amorphized gallium arsenide: Comparison to sputtered and evaporated a-GaAs films. Journal of Non-Crystalline Solids, 1989, 114, 795-797.	3.1	14
36	Effects of ion bombardment on the chemical reactivity of gallium arsenide(100): variation of bombarding ion mass. Chemistry of Materials, 1990, 2, 173-180.	6.7	12

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37	Effect of pressure on a defect-related band-resonant vibrational mode in implantation-disordered GaAs. <i>Physical Review B</i> , 1994, 50, 10702-10705.	3.2	11
38	Properties of carbon-doped low-temperature GaAs and InP grown by solid-source molecular-beam epitaxy using CBr ₄ . <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 1594.	1.6	11
39	Effect of pressure on optical properties of crystalline As ₂ S ₃ . <i>High Pressure Research</i> , 2004, 24, 117-118.	1.2	10
40	Pressure effects on the absorption edge, refractive index, and Raman spectra of crystalline and amorphous As ₂ S ₃ . <i>Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics</i> , 1981, 105, 319-323.	0.9	9
41	New structure in the XPS valence band spectra of the layered crystal As ₂ S ₃ and its amorphous analogues. <i>Societa Italiana Di Fisica Nuovo Cimento B-General Physics, Relativity Astronomy and Mathematical Physics and Methods</i> , 1977, 38, 248-255.	0.2	8
42	Resonant Raman-active acoustic phonons in the mixed amorphous-microcrystalline phase of ion-implanted GaAs. <i>Physical Review B</i> , 1988, 37, 2737-2740.	3.2	7
43	Optical Studies of Nanophase Titania. , 1997, , 395-403.		6
44	Thermal Modulation of HgS Edge Absorption. <i>Journal of Applied Physics</i> , 1972, 43, 2442-2443.	2.5	4
45	Pressure-Raman studies of implantation disordered GaAs. <i>AIP Conference Proceedings</i> , 1994, , .	0.4	1
46	Interband Optical Properties of the Microcrystalline Component within the Damage Layer of Be ⁺ -Implanted GaAs. <i>Materials Research Society Symposia Proceedings</i> , 1988, 128, 671.	0.1	0